The documentation and process conversion measures necessary to comply with this revision shall be completed by 23 August 2019.

INCH-POUND

MIL-PRF-19500/518E
24 MAY 2019
SUPERSEDING
MIL-PRF-19500/518D
w/AMENDMENT 1
2 March 2012

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, NPN, SILICON, POWER,
TYPES 2N3766 AND 2N3767,
QUALITY LEVELS JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for NPN silicon, power transistors. Three levels of product assurance (JAN, JANTX and JANTXV) are provided for each device type as specified in MIL-PRF-19500.

1.2 Package outline. The device package outline is a TO-213AA in accordance with figure 1.

1.3 Maximum ratings. Unless otherwise specified, T_C = +25°C.

Type	P_T (1)	V_{CBO}	V_{CEO}	V_{EBO}	I_B	I_C	T_J and T_{STG}	$R_{\theta JC}$
	W	V dc	V dc	V dc	A dc	A dc	°C	°C/W
2N3766	25	80	60	6	2	4	-65 to +200	7
2N3767	25	100	80	6	2	4	-65 to +200	7

(1) Between T_C = +25°C and T_C = +200°C, linear derating factor (average) = 143 m/W°C.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at https://assist.dla.mil.

AMSC N/A

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